

isc Silicon PNP Power Transistor

2SA1672

DESCRIPTION

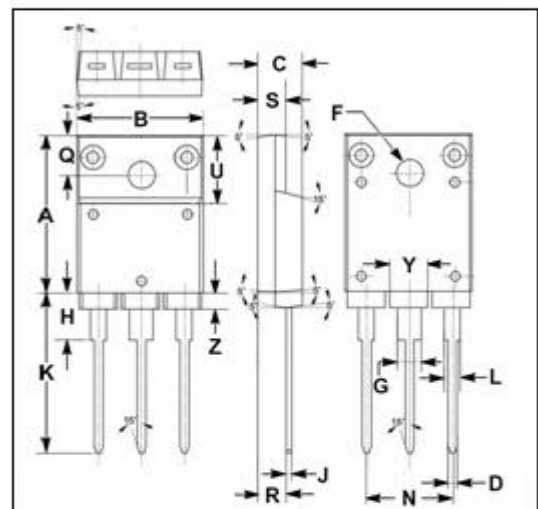
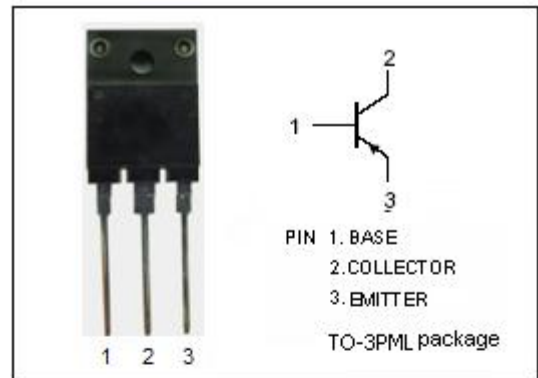
- Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -140V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SC4387

APPLICATIONS

- Designed for audio and general purpose applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-140	V
$V_{CEO}$	Collector-Emitter Voltage	-140	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-10	A
$I_B$	Base Current-Continuous	-4	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

**isc Silicon PNP Power Transistor****2SA1672****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; I_B = 0$	-140			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-2.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -140\text{V}; I_E = 0$			-10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$			-10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -4\text{V}$	50			
$f_T$	Current-Gain—Bandwidth Product	$I_E = 0.5\text{A}; V_{CE} = -12\text{V}$		20		MHz

## Switching times

$t_{on}$	Turn-on Time	$I_C = -5\text{A}, R_L = 12\Omega,$ $I_{B1} = -I_{B2} = -0.5\text{A}, V_{CC} = -60\text{V}$		0.3		$\mu\text{s}$
$t_{stg}$	Storage Time			0.9		$\mu\text{s}$
$t_f$	Fall Time			0.2		$\mu\text{s}$